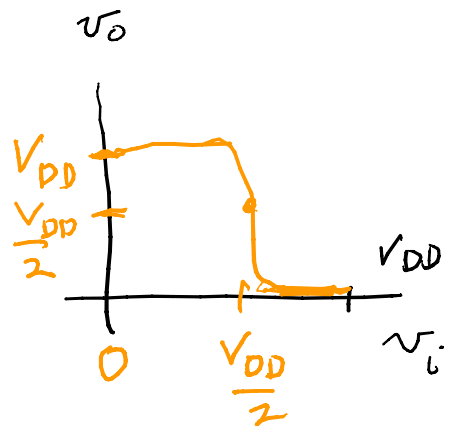
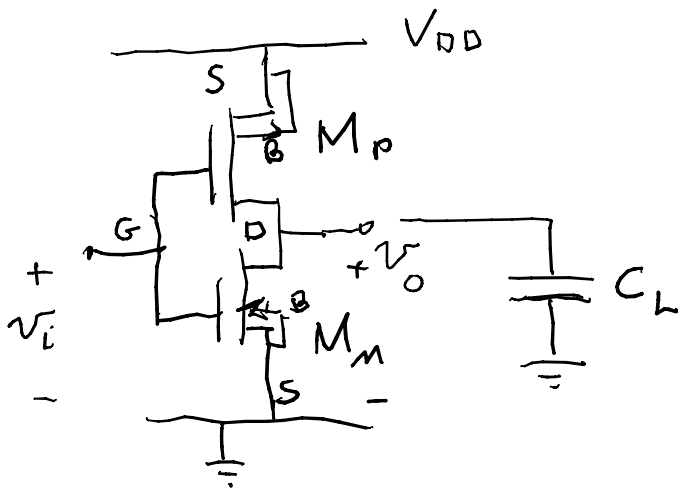


EE 303
03/08/06



state of transistors
need $v_{GS} - V_{th}$ versus v_{DS}

at the transition $v_i = v_o = V_{DD}/2$

if $M_p =$ complement of M_n ; here $V_{th} =$ threshold voltage $= V_{TO}$

$$v_{GS_n} = v_i \quad v_{GS} - V_{TO} \text{ compared to } v_{DS}$$

$$v_{DS_n} = v_o \quad \text{here } v_i - V_{TO_n} \leq v_i = v_o$$

$\Rightarrow M_n$ is in saturation

$$v_{SG_p} = V_{DD} - v_i \quad v_{SG_p} - |V_{TO_p}| \text{ compared to } v_{SD_p}$$

$$v_{SD_p} = V_{DD} - v_o$$

$$V_{DD} - v_i - |V_{TO_p}| < V_{DD} - v_i = v_{SD_p}$$

$\Rightarrow M_p$ is in saturation $= V_{DD} - v_o$

at transition point (with no load)

$$-i_{Dp} = i_{Dn}$$

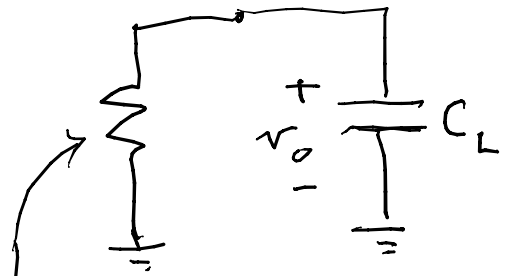
$$\begin{aligned} -i_{Dp} = i_{Sp} &= \frac{Kp_p}{2} \left(\frac{W}{L}\right)_p (v_{SG} - |VTO_p|)^2 \\ &= \frac{Kp_p}{2} \left(\frac{W}{L}\right)_p (V_{DD} - v_i - |VTO_p|)^2 \end{aligned}$$

$$\begin{aligned} i_{Dn} &= \frac{Kp_n}{2} \left(\frac{W}{L}\right)_n (v_{GS} - |VTO_n|)^2 \\ &= \frac{Kp_n}{2} \left(\frac{W}{L}\right)_n (v_i - |VTO_n|)^2 \end{aligned}$$

$$\begin{aligned} i_{Sp} \Big|_{v_i = \frac{V_{DD}}{2}} = i_{Dn} \Big|_{v_i = \frac{V_{DD}}{2}} &\Rightarrow \frac{Kp_p}{2} \left(\frac{W}{L}\right)_p \left(V_{DD} - \frac{V_{DD}}{2} - |VTO_p|\right)^2 \\ &= \frac{Kp_n}{2} \left(\frac{W}{L}\right)_n \left(\frac{V_{DD}}{2} - |VTO_n|\right)^2 \end{aligned}$$

$$\Rightarrow \left(\frac{W}{L}\right)_p = \left(\frac{W}{L}\right)_n \times \frac{Kp_n}{Kp_p} \times \left(\frac{\frac{V_{DD}}{2} - |VTO_n|}{\frac{V_{DD}}{2} - |VTO_p|}\right)^2$$

This allows design of inverters to transition at $v_i = v_o = \frac{V_{DD}}{2}$ by design of M_p given M_n



ave R seen
by C_L
when
discharge

$v_o(0+) = V_{DD}$
 $v_o(\infty) = 0$
as invert

